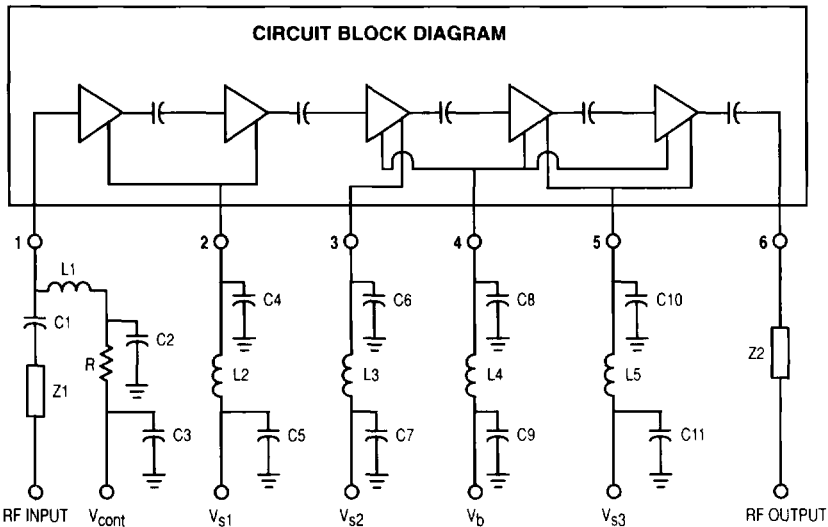


ELECTRICAL CHARACTERISTICS — continued MHW914 — $V_{S2} = V_{S3} = 12.5$ Vdc; $V_{S1} = V_b = 8.0$ Vdc;
MHW915 — $V_{S1} = V_{S2} = V_{S3} = 12.5$ Vdc; $V_b = 5.0$ Vdc ($T_C = 25^\circ\text{C}$, 50 ohm system, unless otherwise noted)

Characteristic	Symbol	Min	Max	Unit
Noise Power (In 30 kHz Bandwidth, 20 MHz above f_o) ($P_{out} = 0.03$ to 14 W, $V_{S2} = V_{S3} = 10.8$ to 15.6 Vdc, $P_{in} = 1.0$ mW) MHW914 (1) ($P_{out} = 0.03$ to 14 W, $V_{S1} = V_{S2} = V_{S3} = 10.8$ to 15.6 Vdc) MHW915 (2)	—	—	-70	dBm
3.0 dB V_{cont} Bandwidth ($P_{in} = 1.0$ mW, $P_{out} = 0.03$ to 14 W) MHW914 only	—	1.0	—	MHz
Output Power Reduced Voltage ($P_{in} = 1.0$ mW; $V_{S2} = V_{S3} = 10.8$ Vdc) MHW914 ($P_{in} = 100$ mW; $V_{S1} = V_{S2} = V_{S3} = 10.8$ Vdc) MHW915	P_{OUT2}	10	—	W
Linearity — % AM in Output ($P_{out} = 0.02$ to 14 W; 135 kHz, 1% AM on Input) MHW915 only (2)	—	—	6.0	%
Load Mismatch Stress ($V_{S2} = V_{S3} = 15.6$ Vdc, $P_{in} = 3.0$ mW, $P_{out} = 15$ W) MHW914 (1) ($V_{S1} = V_{S2} = V_{S3} = 15.6$ Vdc, $P_{out} = 15$ W) MHW915 (2) (Load VSWR = 10:1, All Phase Angles at Frequency of Test)	ψ	No degradation in output power before and after test		
Stability ($V_{S2} = V_{S3} = 10.8$ to 15.6 Vdc; $P_{in} = 0.5$ to 3.0 mW; $P_{out} = 0$ mW to 14 W) MHW914 (1) ($V_{S1} = V_{S2} = V_{S3} = 10.8$ to 15.6 Vdc, $P_{out} = 0.03$ to 14 W) MHW915 (2) (Load VSWR = 6:1, Source VSWR = 3:1, All Phase Angles at Frequency of Test)	—	All spurious outputs more than 60 dB below desired signal		

NOTES:

1. Adjust V_{cont} for specified P_{out} ; duty cycle = 12.5%, period = 4.6 ms
2. Adjust P_{in} for specified P_{out} ; duty cycle = 12.5%, period = 4.6 ms



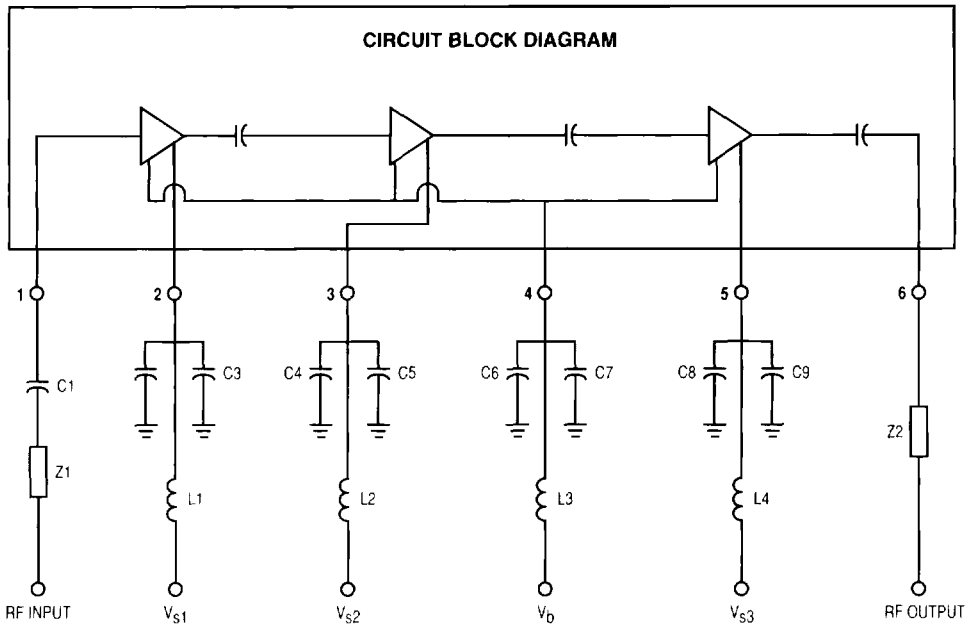
PIN DESIGNATIONS:

- Pin 1 — RF Input Power @ 0 dBm and Control Voltage @ 0–3.0 Vdc
- Pin 2 — First and Second Stage Collector Supply Voltage @ 8.0 Vdc
- Pin 3 — Third Stage Collector Voltage @ 12.5 Vdc
- Pin 4 — Trickle Bias Voltage @ 8.0 Vdc
- Pin 5 — Fourth and Fifth Stage Collector Supply Voltage @ 12.5 Vdc
- Pin 6 — RF Output Power @ 14 W

ELEMENT VALUES:

- $C1=C4=C6=C8=C10 = 0.018$ μF
- $C2=0.1$ μF
- $C3=C5=C7=C9=C11 = 1.0$ μF
- $L1-L4 = 0.29$ μH
- $L5 = 0.2$ μH
- $R = 20$ Ohms
- $Z1, Z2 = 50$ Ohm Microstrip

Figure 1. Test Circuit Diagram — MHW914



PIN DESIGNATIONS:

- Pin 1 — RF Input Power @ 20 dBm Max Adjust for Output Power
- Pin 2 — First Stage Collector Voltage @ 12.5 Vdc
- Pin 3 — Second Stage Collector Voltage @ 12.5 Vdc
- Pin 4 — Trickle Bias Voltage @ 5.0 Vdc
- Pin 5 — Third Stage Collector Supply @ 12.5 Vdc
- Pin 6 — RF Output Power @ 14 W Nominal

ELEMENT VALUES:

- C1=C2=C4=C6=C8 = 0.018 μ F
- C3=C5=C7=C9 = 2.2 μ F
- L1-L3 = 0.29 μ H
- L4 = 0.2 μ H
- Z1, Z2 = 50 Ohm Microstrip

Figure 2. Test Circuit Diagram — MHW915

TYPICAL CHARACTERISTICS (MHW914)

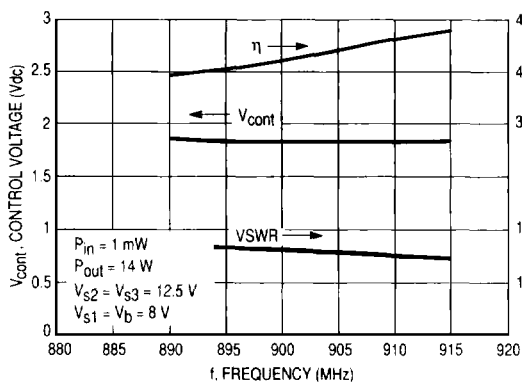


Figure 3. Control Voltage, Efficiency and Input VSWR versus Frequency

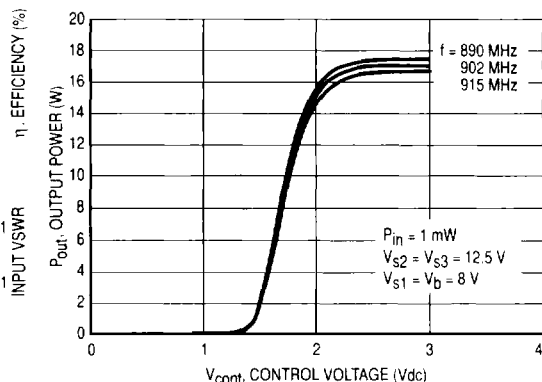


Figure 4. Output Power versus Control Voltage

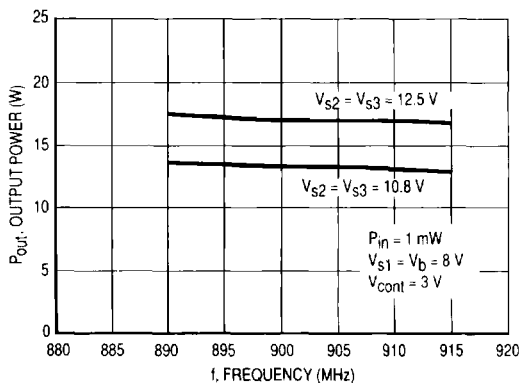


Figure 5. Output Power versus Frequency

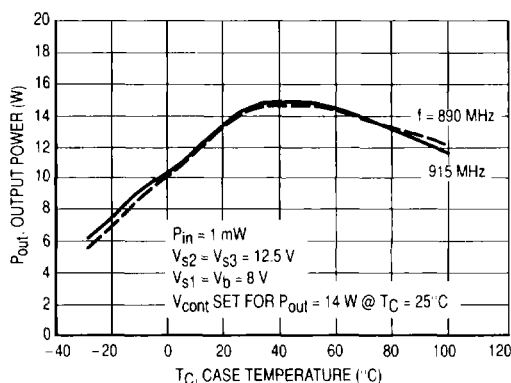


Figure 6. Output Power versus Case Temperature

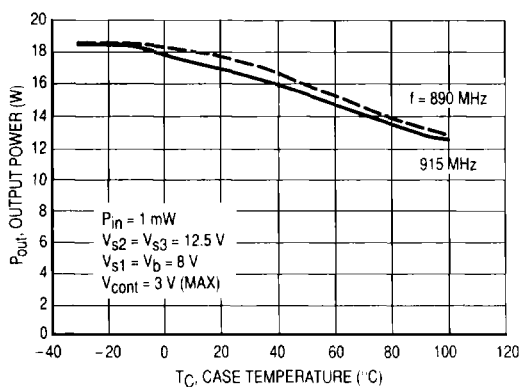


Figure 7. Output Power versus Case Temperature at Maximum Control Voltage

TYPICAL CHARACTERISTICS (MHW915)

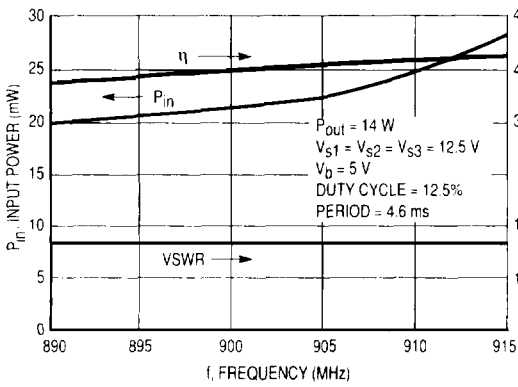


Figure 8. Input Power, Efficiency and Input VSWR versus Frequency

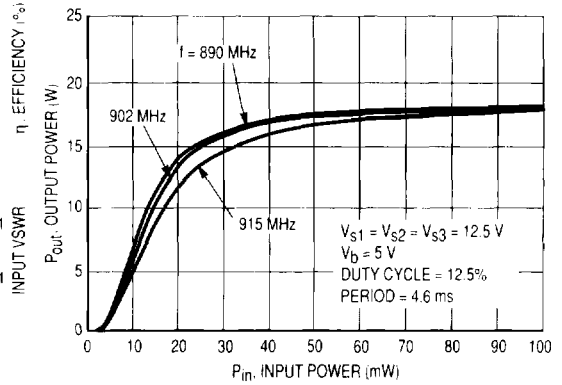


Figure 9. Output Power versus Input Power

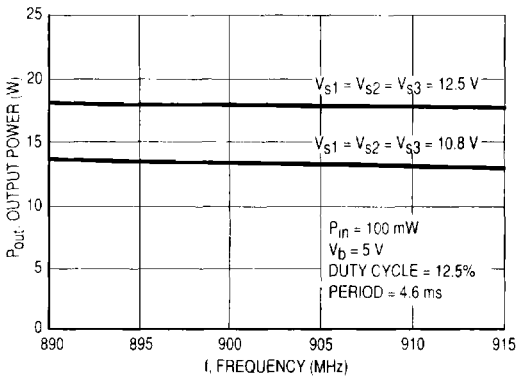


Figure 10. Output Power versus Frequency

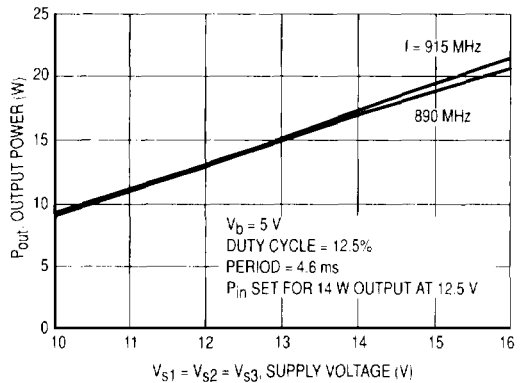


Figure 11. Output Power versus Supply Voltage

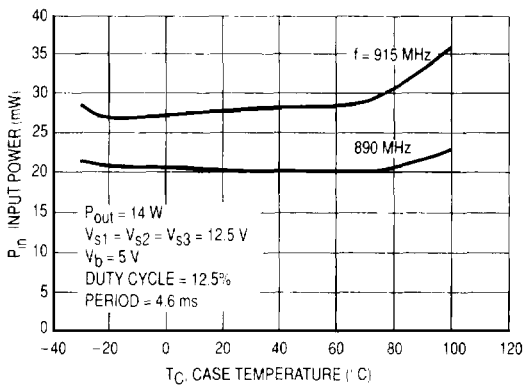


Figure 12. Input Power versus Case Temperature for $P_{out} = 14\text{ W}$

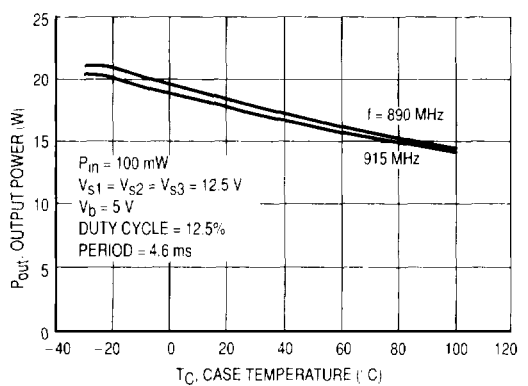


Figure 13. Output Power versus Case Temperature for Maximum Input Power

APPLICATIONS INFORMATION

NOMINAL OPERATION

For the MHW914, all electrical specifications are based on the nominal conditions of $V_b = V_{S1} = 8.0$ Vdc (Pins 2, 4), and $V_{S2} = V_{S3} = 12.5$ Vdc (Pins 3, 5). For the MHW915 the nominal conditions are $V_{S1} = V_{S2} = V_{S3} = 12.5$ Vdc (Pins 2, 3, 5) and $V_b = 5.0$ Vdc (Pin 4). With these conditions, maximum current density on any device is 1.5×10^5 A/cm² and maximum die temperature is 165°C. While the modules are designed to have excess gain margin with ruggedness, operation of these units outside the published specifications is not recommended unless prior communications regarding intended use have been made with the factory representative.

GAIN CONTROL

The module output power should be limited to specified value. The preferred method of power control for the MHW914 is to fix $V_b = V_{S1} = 8.0$ Vdc, $V_{S2} = V_{S3} = 12.5$ Vdc, P_{in} (Pin 1) at 1.0 mW, and vary V_{cont} (Pin 1) voltage. The preferred method for the MHW915 is to fix all voltages at nominal and vary P_{out} (Pin 6) by changing P_{in} (Pin 1) from 0 to 100 mW.

DECOUPLING

Due to the high gain of the five stages and the module size limitation, external decoupling networks require careful consideration, Pins 2, 3, 4 and 5 are internally bypassed with a 0.018 μ F chip capacitor which is effective for frequencies from 5.0 MHz through 940 MHz. For bypassing frequencies below 5.0 MHz, networks equivalent to that shown in Figure 1 and Figure 2 are recommended. Inadequate decoupling will result in spurious outputs at certain operating frequencies and certain phase angles of input and output VSWR.

LOAD MISMATCH

During final test each module is load mismatch tested in a fixture having the identical decoupling networks described in Figures 1 and 2 for the MHW914 and MHW915 respectively. Electrical conditions are $V_b = V_{S1} = 8.0$ V (Pins 2, 4) and $V_{S2} = V_{S3} = 15.6$ Vdc (Pins 3, 5) for the MHW914 and $V_{S1} = V_{S2} = V_{S3} = 15.6$ Vdc (Pins 2, 3, 5) and $V_b = 5.0$ Vdc (Pin 4) for the MHW915. $P_{out} = 15$ W, $P_{in} = 3.0$ mW, load VSWR equals 10:1 at all phase angles for both modules.